PHD66NQ03LT

N-channel TrenchMOS logic level FET

Rev. 07 — 30 June 2009 **Product data sheet**

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC convertors
- General purpose switching

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	-	25	V
I_D	drain current	$T_{mb} = 25$ °C; $V_{GS} = 10$ V	-	-	66	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2	-	-	93	W
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 5$ V; $I_D = 50$ A; $V_{DS} = 15$ V; $T_j = 25$ °C; see Figure 11	-	3.6	-	nC
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10$ V; $I_D = 25$ A; $T_j = 25$ °C; see Figure 9; see Figure 10	-	9.1	10.5	mΩ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	SOT428 (DPAK)	
2	D	drain [1]		
3	S	source		
mb	D	mounting base; connected to drain		

[1] It is not possible to make a connection to pin 2

3. Ordering information

Table 3. Ordering information

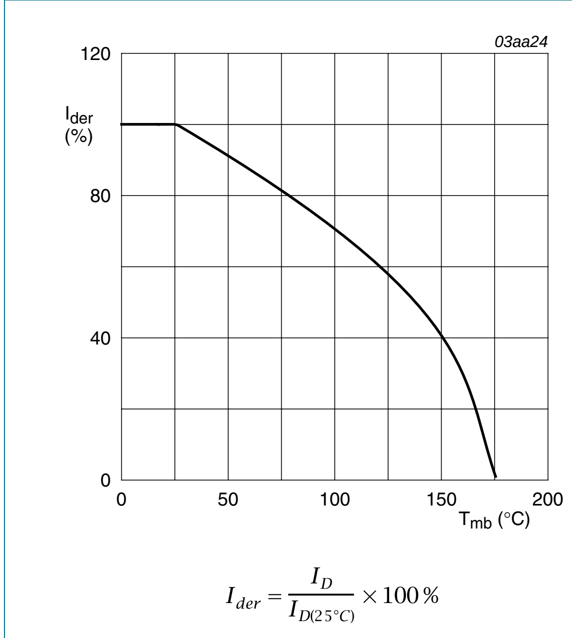
Type number	Package		
	Name	Description	Version
PHD66NQ03LT	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

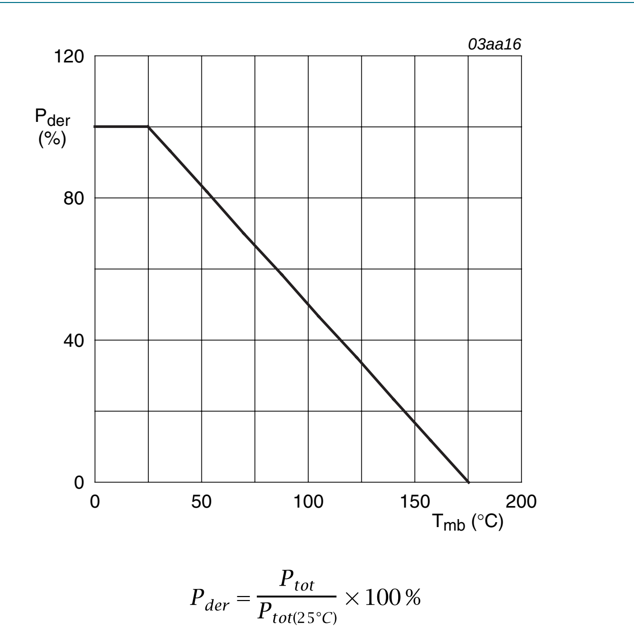
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	25	V
V_{DGR}	drain-gate voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C; $R_{GS} = 20$ kΩ	-	25	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10$ V; $T_{mb} = 100$ °C	-	45	A
		$V_{GS} = 5$ V; $T_{mb} = 100$ °C; see Figure 1	-	40	A
		$V_{GS} = 5$ V; $T_{mb} = 25$ °C; see Figure 1; see Figure 3	-	57	A
		$V_{GS} = 10$ V; $T_{mb} = 25$ °C	-	66	A
I_{DM}	peak drain current	$t_p \leq 10$ µs; pulsed; $T_{mb} = 25$ °C; see Figure 3	-	228	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2	-	93	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25$ °C	-	57	A
I_{SM}	peak source current	$t_p \leq 10$ µs; pulsed; $T_{mb} = 25$ °C	-	228	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 43$ A; $V_{sup} \leq 25$ V; unclamped; $t_p = 0.15$ ms; $R_{GS} = 50$ Ω	-	90	mJ



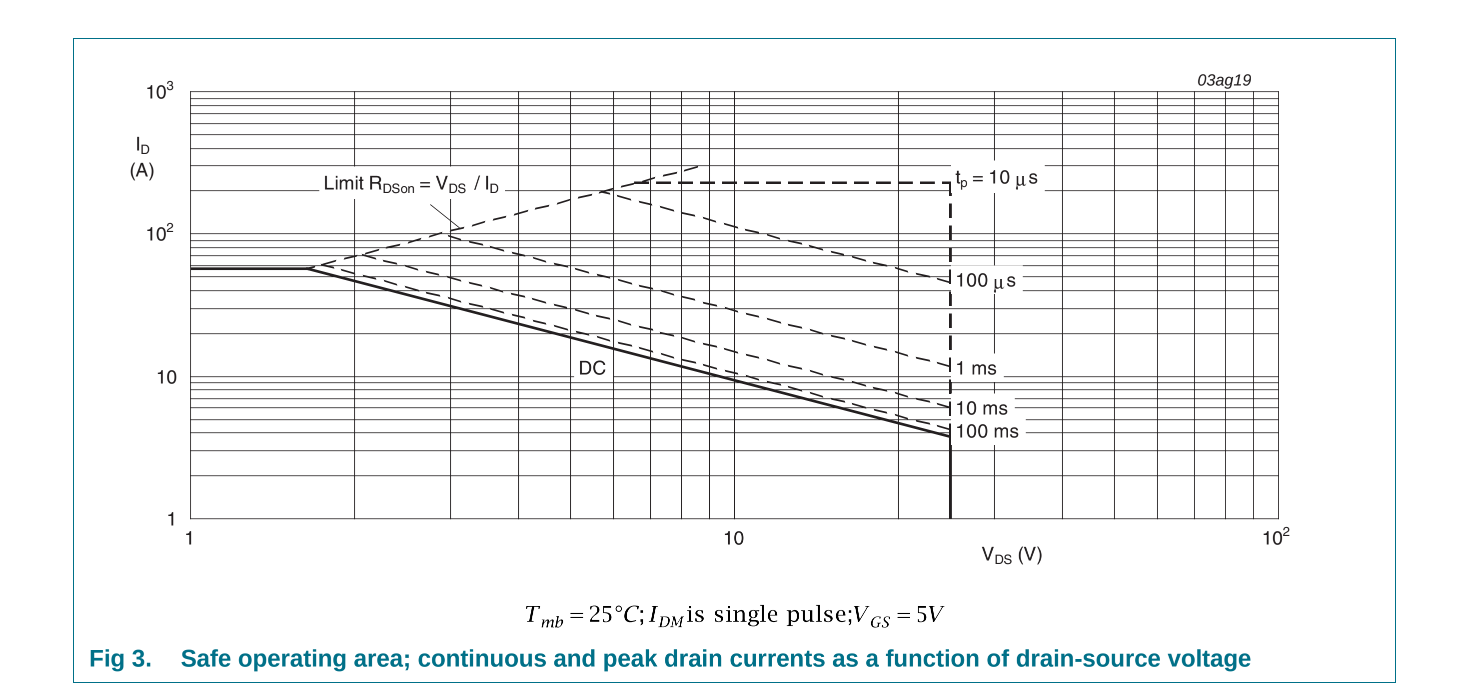
$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\,\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25°C; I_{DM}$ is single pulse; $V_{GS} = 5V$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	75	-	K/W

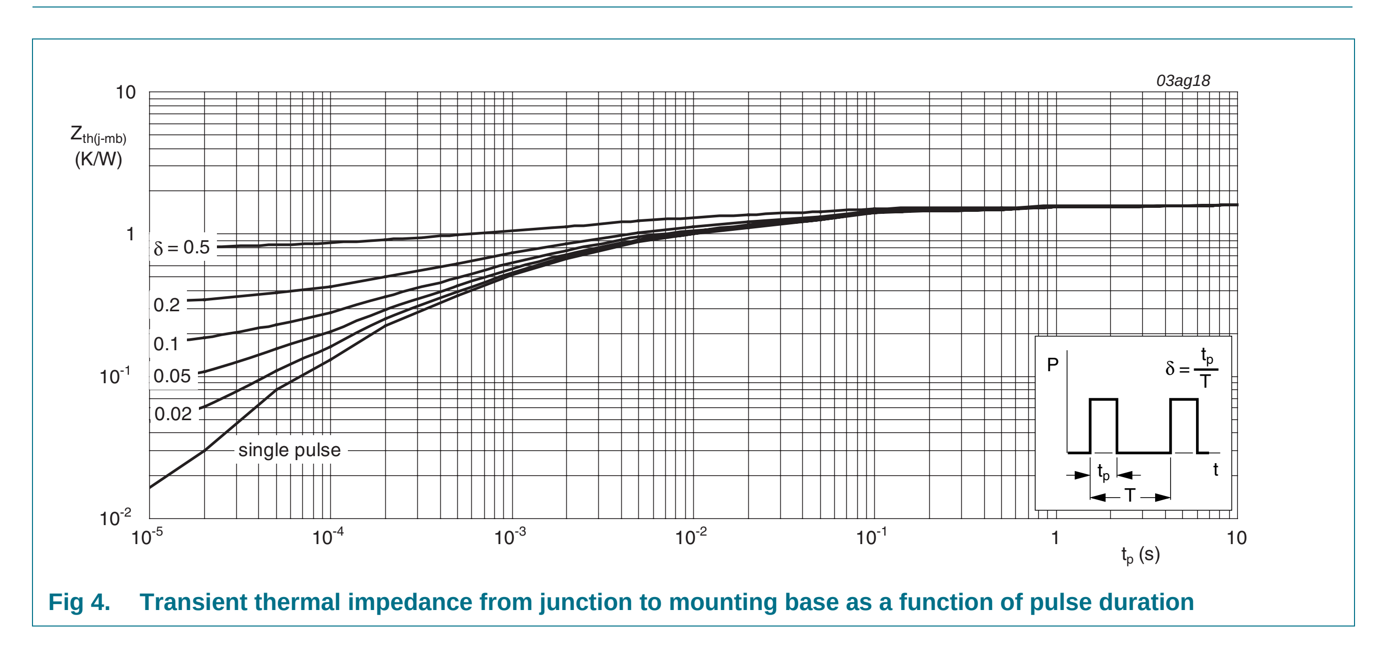
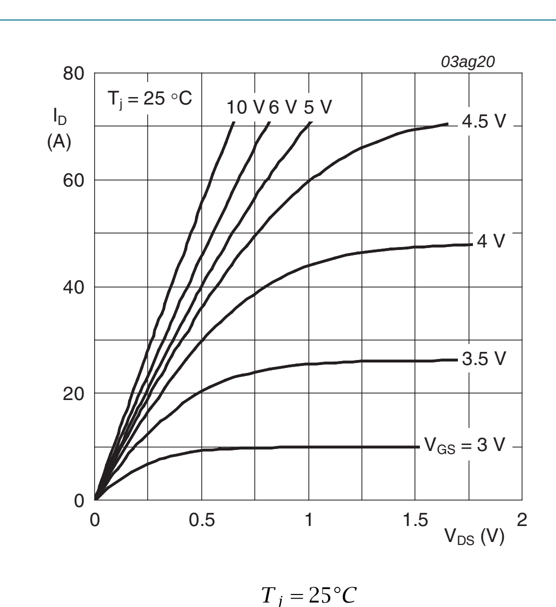


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

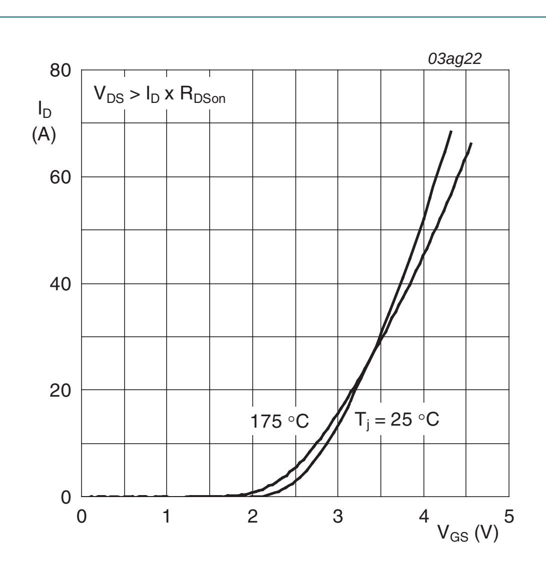
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 μA; V_{GS} = 0 V; T_j = -55 °C	22	-	-	V
		I_D = 250 μA; V_{GS} = 0 V; T_j = 25 °C	25	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 7; see Figure 8	-	-	2.2	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 7; see Figure 8	0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 7; see Figure 8	1	1.5	2	V
I_{DSS}	drain leakage current	V_{DS} = 25 V; V_{GS} = 0 V; T_j = 25 °C	-	-	10	μA
		V_{DS} = 25 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I_{GSS}	gate leakage current	V_{GS} = 15 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = -15 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 9; see Figure 10	-	16.4	18.9	mΩ
		V_{GS} = 5 V; I_D = 25 A; T_j = 25 °C; see Figure 9; see Figure 10	-	11.2	13.6	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 9; see Figure 10	-	9.1	10.5	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 50 A; V_{DS} = 15 V; V_{GS} = 5 V; T_j = 25 °C; see Figure 11	-	12	-	nC
Q_{GS}	gate-source charge		-	4.5	-	nC
Q_{GD}	gate-drain charge		-	3.6	-	nC
C_{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 12	-	860	-	pF
C_{oss}	output capacitance		-	330	-	pF
C_{rss}	reverse transfer capacitance		-	145	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 15 V; R_L = 0.6 Ω; V_{GS} = 5 V; $R_{G(ext)}$ = 5.6 Ω; T_j = 25 °C	-	15	25	ns
t_r	rise time		-	90	135	ns
$t_{d(off)}$	turn-off delay time		-	25	40	ns
t_f	fall time		-	25	40	ns
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 13	-	0.95	1.2	V
t_{rr}	reverse recovery time	I_S = 10 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 °C	-	32	-	ns
Q_r	recovered charge		-	20	-	nC



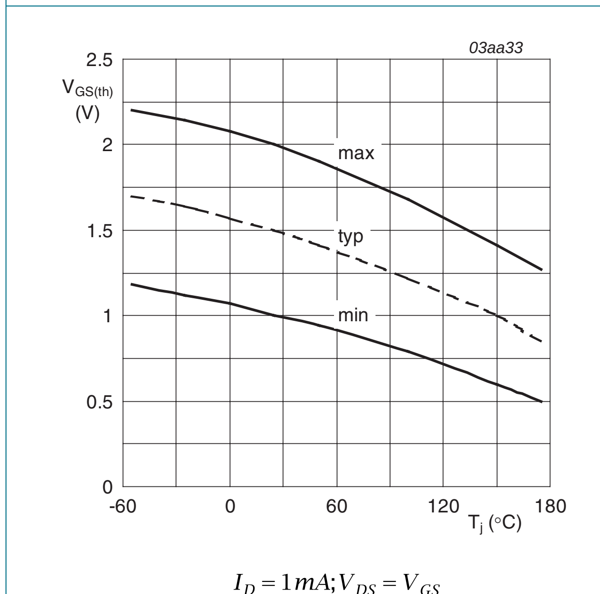
$T_j = 25°C$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



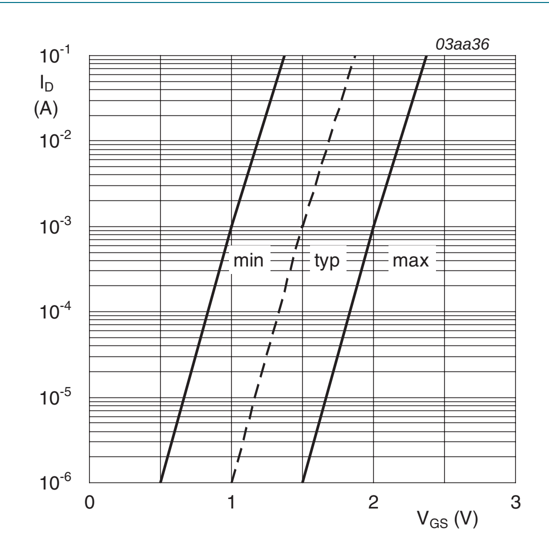
$T_j = 25°C$ and $175°C; V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



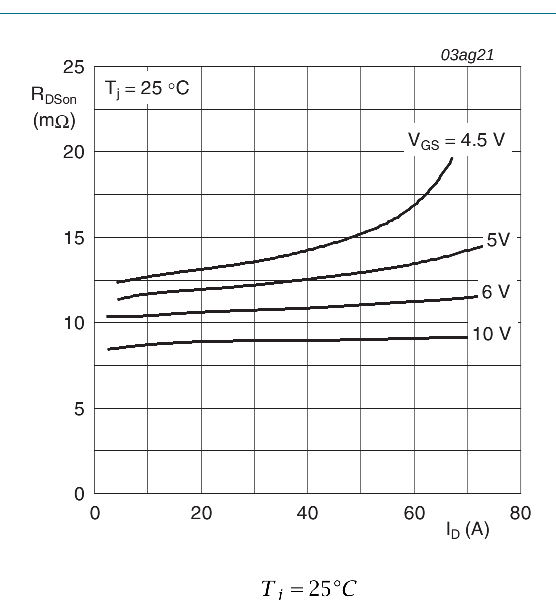
$I_D = 1mA; V_{DS} = V_{GS}$

Fig 7. Gate-source threshold voltage as a function of junction temperature



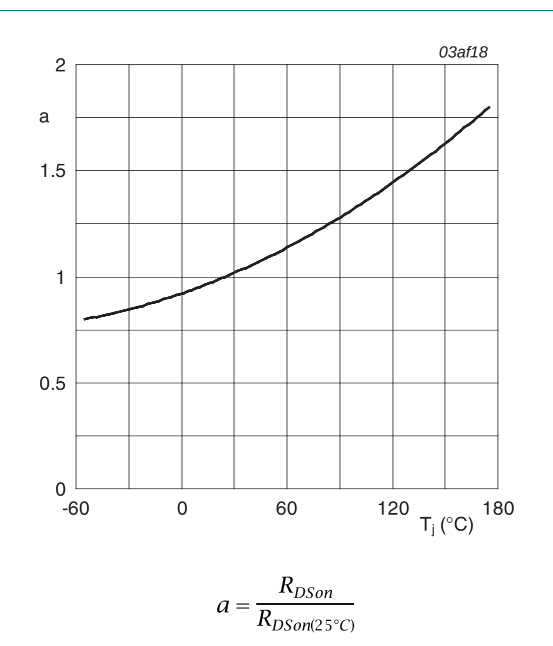
$T_j = 25°C; V_{DS} = V_{GS}$

Fig 8. Sub-threshold drain current as a function of gate-source voltage



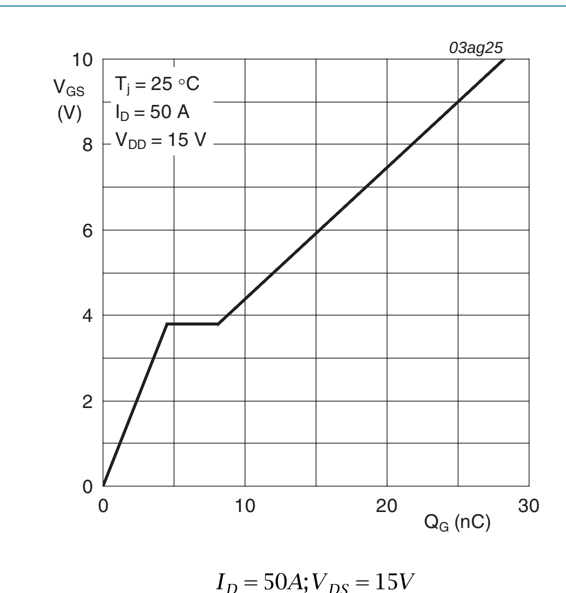
$T_j = 25°C$

Fig 9. Drain-source on-state resistance as a function of drain current; typical values



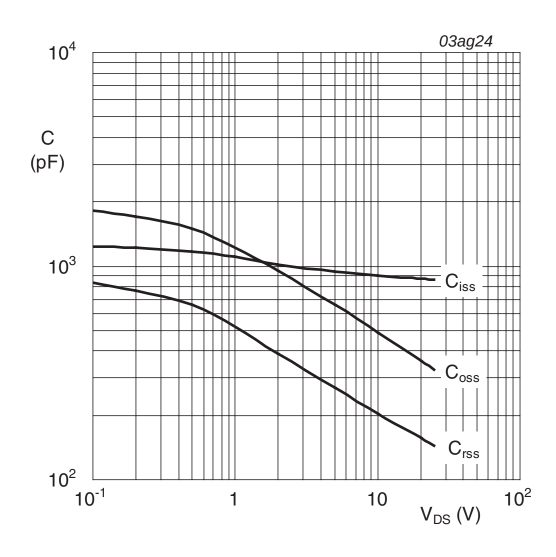
$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



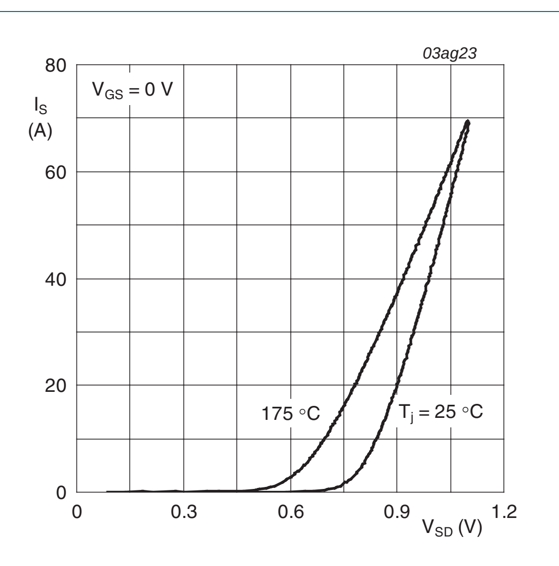
$I_D = 50A; V_{DS} = 15V$

Fig 11. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V; f = 1MHz$

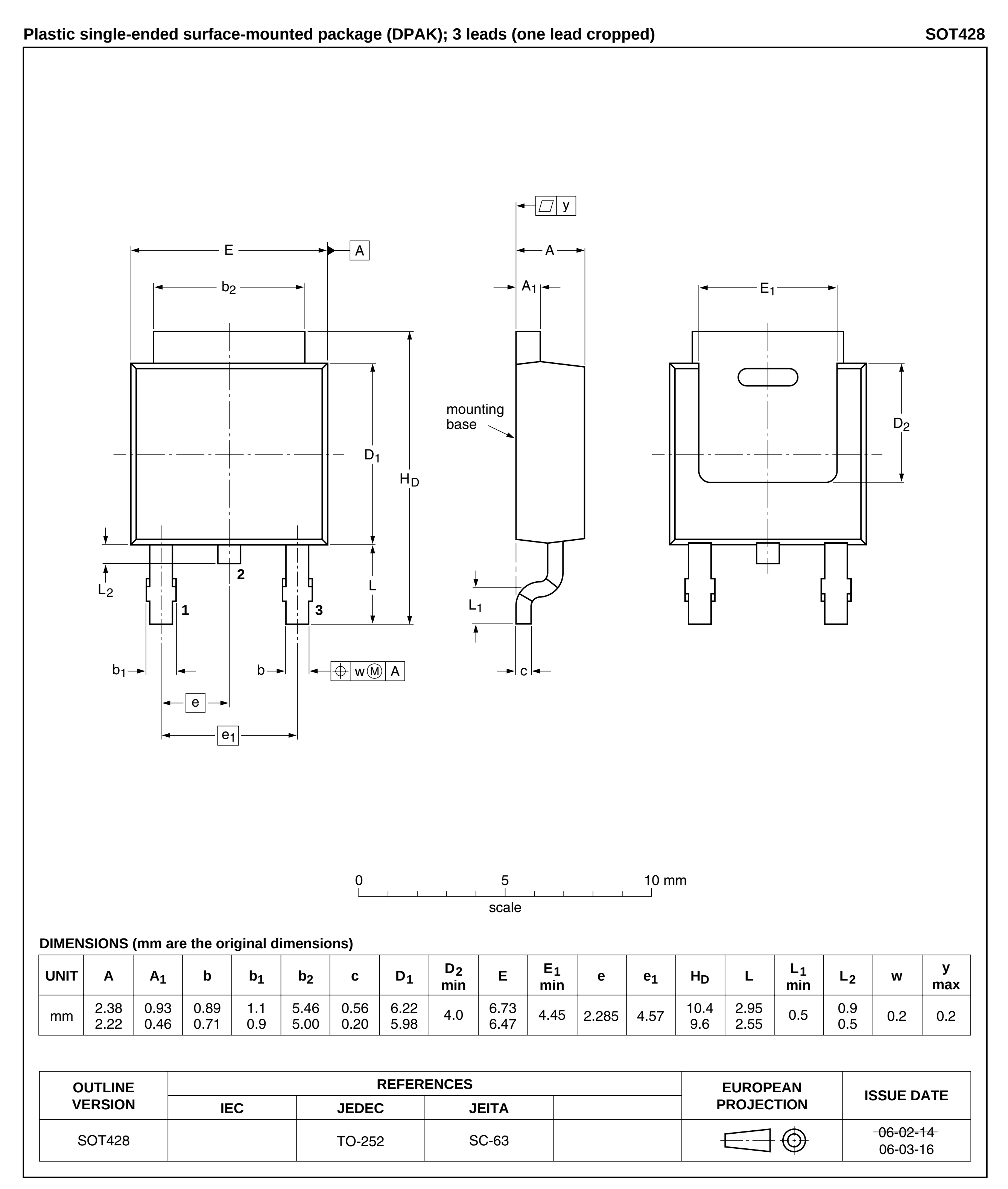
Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$T_j = 25°C$ and $175°C; V_{GS} = 0 V$

Fig 13. Source current as a function of source-drain voltage; typical values

7. Package outline



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	b_2	c	D_1	D_2 min	E	E_1 min	e	e_1	H_D	L	L_1 min	L_2	w	y max
mm	2.38 2.22	0.93 0.46	0.89 0.71	1.1 0.9	5.46 5.00	0.56 0.20	6.22 5.98	4.0	6.73 6.47	4.45	2.285	4.57	10.4 9.6	2.95 2.55	0.5	0.9 0.5	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT428		TO-252	SC-63			~~06-02-14~~ 06-03-16

Fig 14. Package outline SOT428 (DPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHD66NQ03LT_7	20090630	Product data sheet	-	PHB_PHD66NQ03LT_6
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Type number PHD66NQ03LT separated from data sheet PHB_PHD66NQ03LT_6.			
PHB_PHD66NQ03LT_6 (9397 750 13429)	20040802	Product data sheet	-	PHP_PHB_PHD66NQ03LT_5
PHP_PHB_PHD66NQ03LT_5 (9397 750 13107)	20040415	Product data sheet	-	PHP_PHB_PHD66NQ03LT_4
PHP_PHB_PHD66NQ03LT_4 (9397 750 10158)	20020909	Product data sheet	-	PHP_PHB_PHD66NQ03LT_3
PHP_PHB_PHD66NQ03LT_3 (9397 750 09284)	20020312	Product data sheet	-	PHP_PHB_PHD66NQ03LT_2
PHP_PHB_PHD66NQ03LT_2 (9397 750 09119)	20011210	Product data sheet	-	PHP_PHB_PHD66NQ03LT_1
PHP_PHB_PHD66NQ03LT_1 (9397 750 08725)	20011012	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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11. Contents





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